

SDB310Q

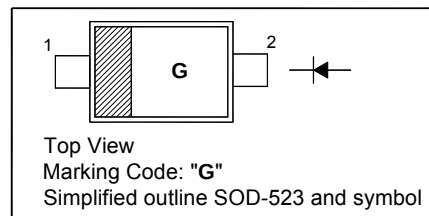
SCHOTTKY BARRIER DIODE

Features

- Low power rectified
- Silicon epitaxial type
- High reliability

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Forward Current	I_F	0.2	A
Repetitive Peak Forward Current	I_{FRM}	0.5	A
Non-Repetitive Peak Forward Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$ at $I_F = 30\text{ mA}$	V_F	0.4 0.5	V
Reverse Current at $V_R = 30\text{ V}$	I_R	1	μA
Total Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	10	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{RR} = 1\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	5	ns

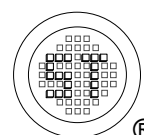


Fig. 1 I_F - V_F

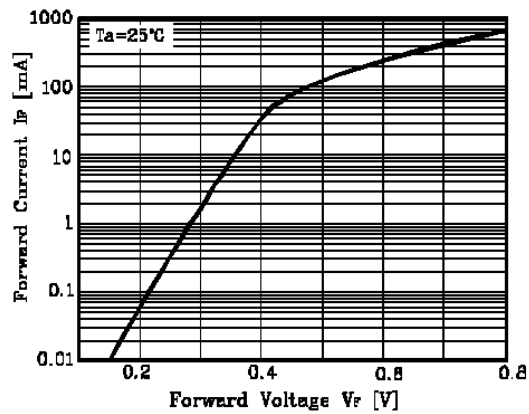


Fig. 2 I_R - V_R

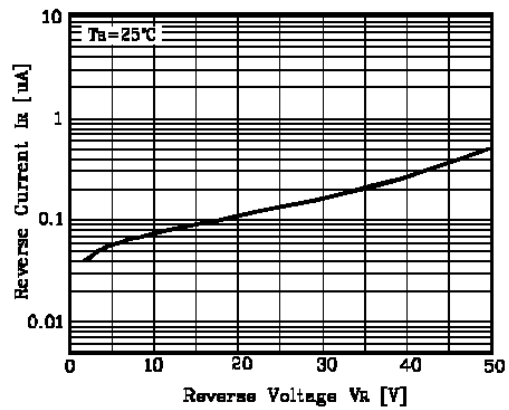
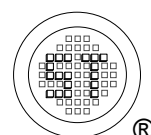
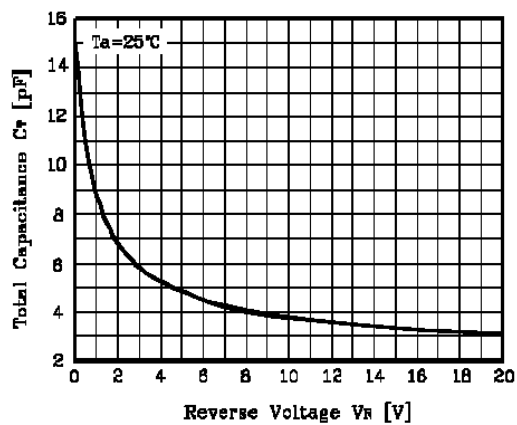


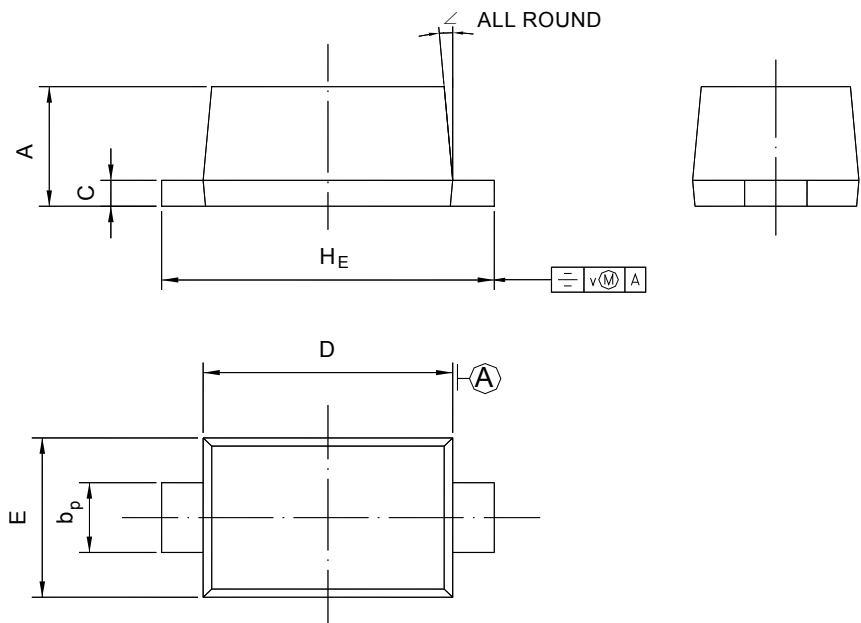
Fig. 3 C_T - V_R



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

